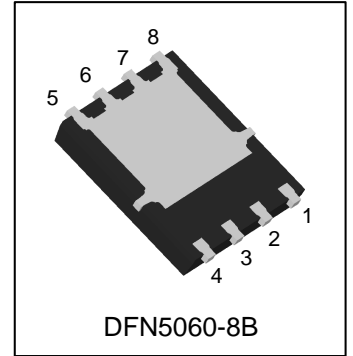


S-LN74025DT3WG

40V N-Channel Power MOSFET

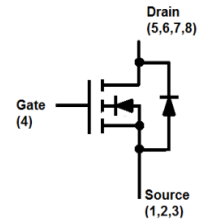


1. FEATURES

- Low thermal impedance.
- Fast switching.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S-prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. APPLICATIONS

- Power Tools
- DC/DC conversion
- Motor Control



3. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
S-LN74025DT3WG	LN74025	5000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-to-Source Voltage		VDS	40	V
Gate-to-Source Voltage		VGS	±20	V
Continuous Drain Current(Note 1)	TA=25°C	ID	34	A
	TA=70°C		27.4	
	TA=100°C		21.4	
Pulsed Drain Current (Note 2)		IDM	136	
Continuous Drain Current	TC=25°C	ID	161.4	A
	TC=70°C		129.1	
	TC=100°C		102.1	
Pulsed Drain Current		IDM	645	
Avalanche Current		IAS	42.6	A
Avalanche Energy(L=0.1mH)		EAS	90.7	mJ
Power Dissipation(Note 1)	TA=25°C	PD	2.8	W
	TC=25°C		62.5	
Operating Junction and Storage Temperature Range		Tj/Tstg	-55~+150	°C

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Thermal Resistance,Junction-to-Ambient(Note 1)	RθJA	45	°C/W
Thermal Resistance,Junction-to-Case	RθJC	2	

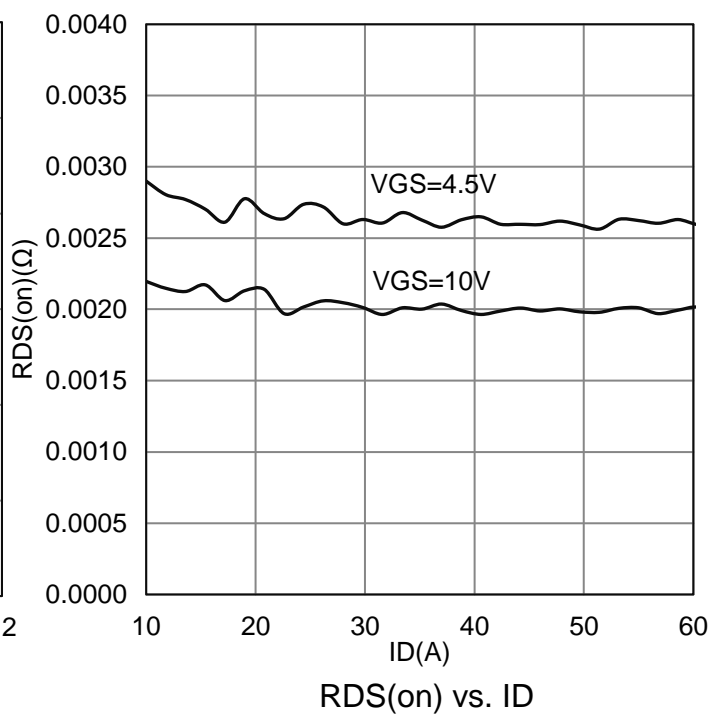
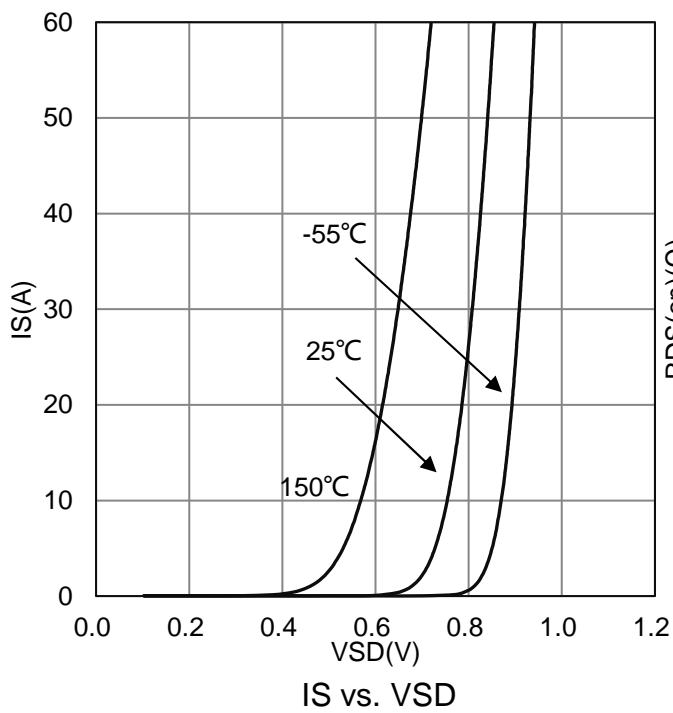
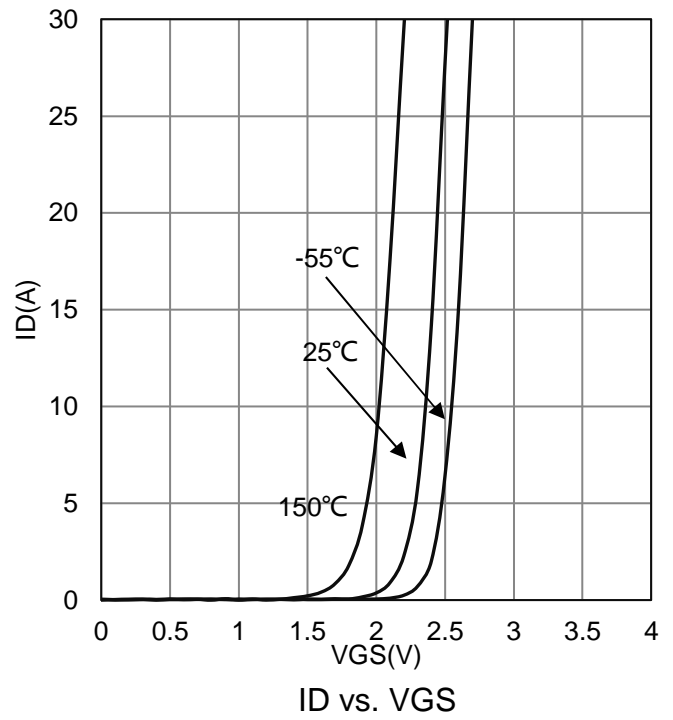
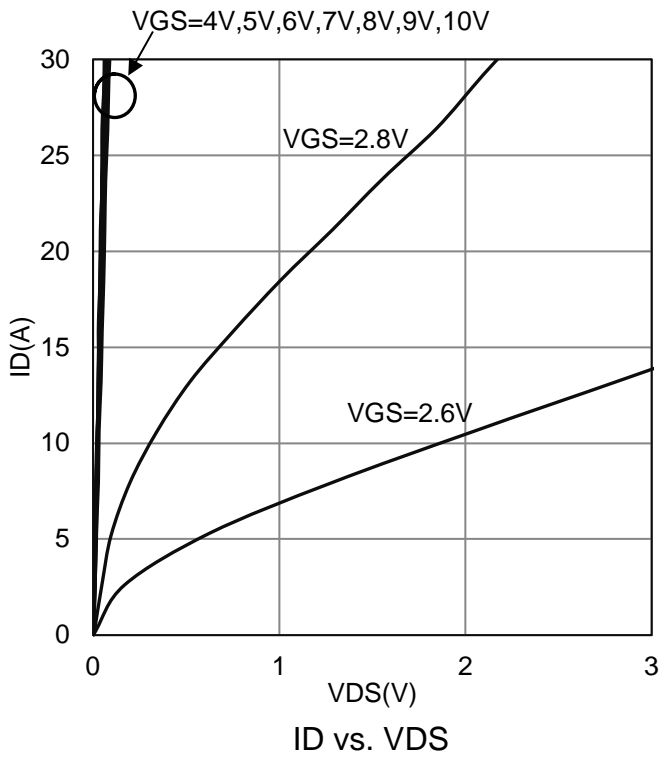
- 1.Surface mounted on 1.5 x 1.5 FR4 board using 1 sq in pad, 2 oz Cu.
- 2.Pulse width limited by maximum junction temperature

6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

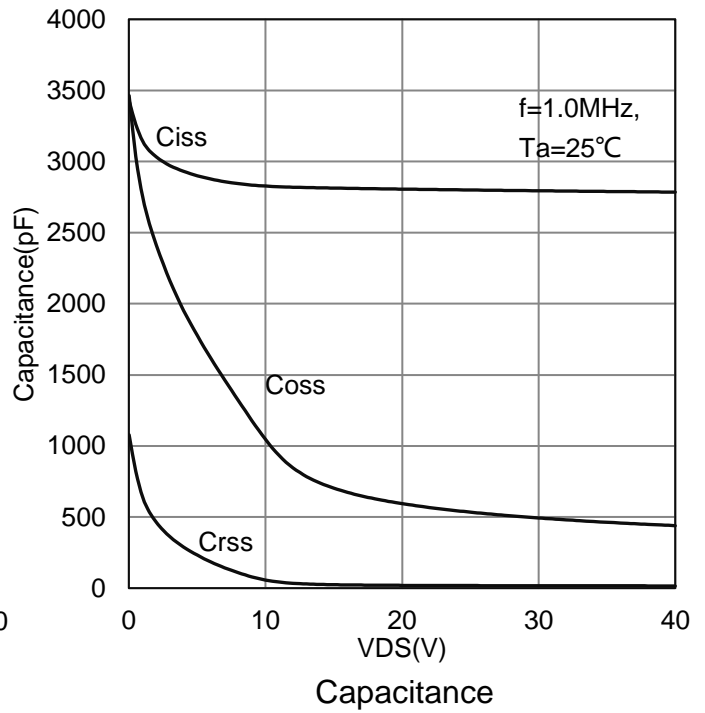
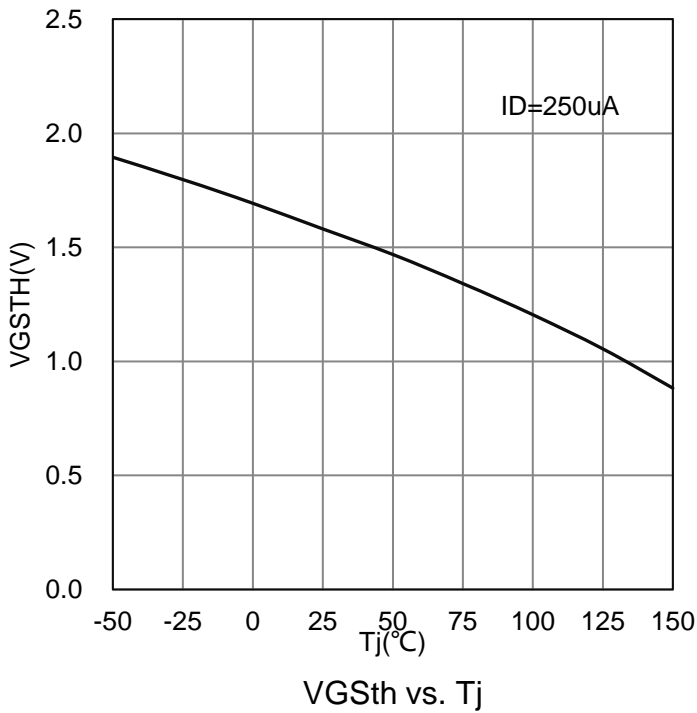
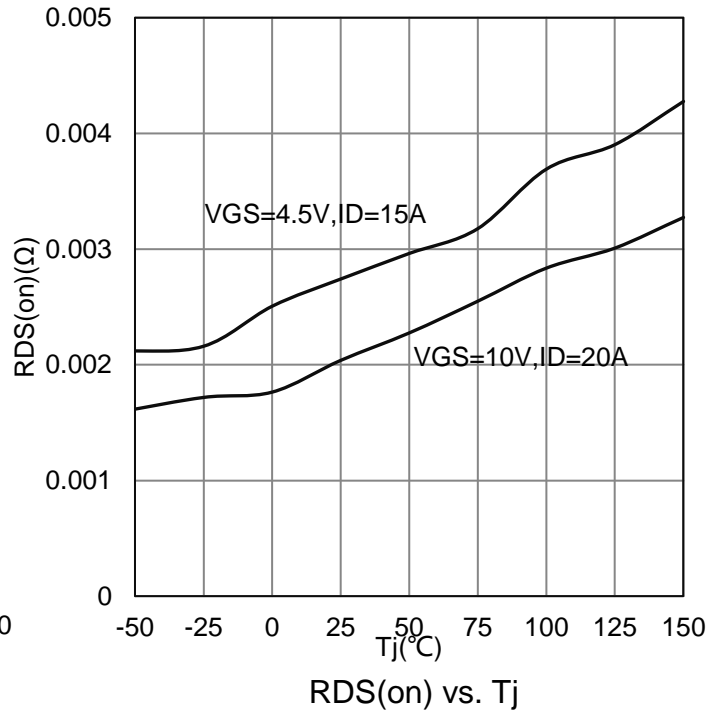
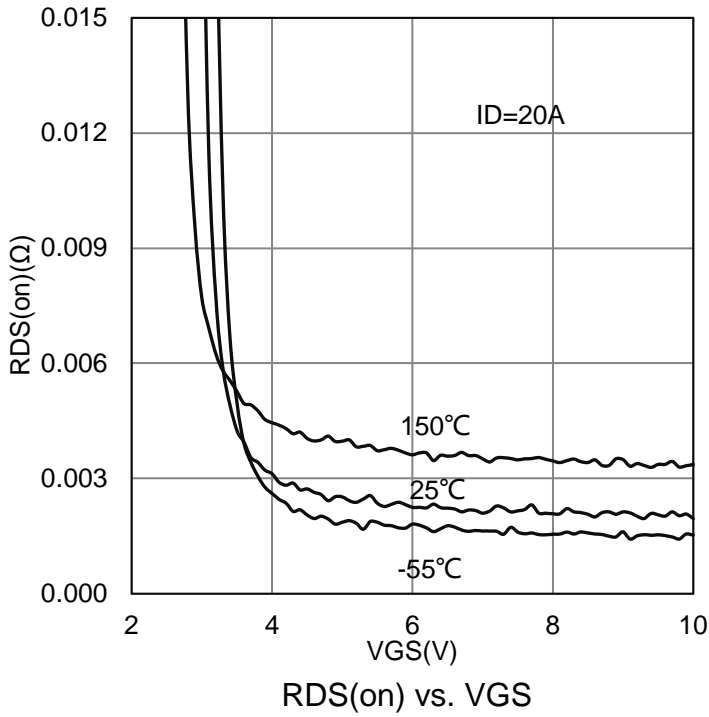
Characteristic	Symbol	Min.	Typ.	Max.	Unit	
STATIC						
Drain–Source Breakdown Voltage (VGS = 0 V, ID = 250 μA)	VBRDSS	40	-	-	V	
Gate Threshold Voltage (VDS = VGS, ID = 250 μA)	VGS(th)	1.2	1.8	2.5	V	
Gate-Body leakage current (VDS = 0 V, VGS = ±20 V)	IGSS	-	-	±100	nA	
Zero Gate Voltage Drain Current (VDS = 32 V, VGS = 0 V)	IDSS	-	-	1	μA	
Drain-to-Source On-Resistance (Note 3) (VGS = 10 V, ID = 20 A) (VGS = 4.5 V, ID = 15 A)	RDS(on)	- -	2.1 2.6	2.5 3	mΩ	
Diode Forward Voltage (IS = 20 A, VGS = 0 V)	VSD	-	0.9	1.2	V	
DYNAMIC						
Total Gate Charge	(VDS = 20 V, VGS = 10 V, ID = 20 A)	Qg	-	46	69	nC
Gate to Source Charge		Qgs	-	8.5	-	
Gate to Drain Charge		Qgd	-	7.6	-	
Turn-on Delay Time	(VDD = 20 V, ID = 20 A, VGS = 10 V, RG = 6 Ω)	td(on)	-	17	-	nS
Rise Time		tr	-	12	-	
Turn-Off Delay Time		td(off)	-	76	-	
Fall Time		tf	-	19	-	
Input Capacitance	(VDS = 20 V, VGS = 0 V, f = 1MHz)	Ciss	-	2825	-	pF
Output Capacitance		Coss	-	605	-	
Reverse Transfer Capacitance		Crss	-	22	-	

3. Pulse test: PW ≤ 300μs duty cycle ≤ 2%.

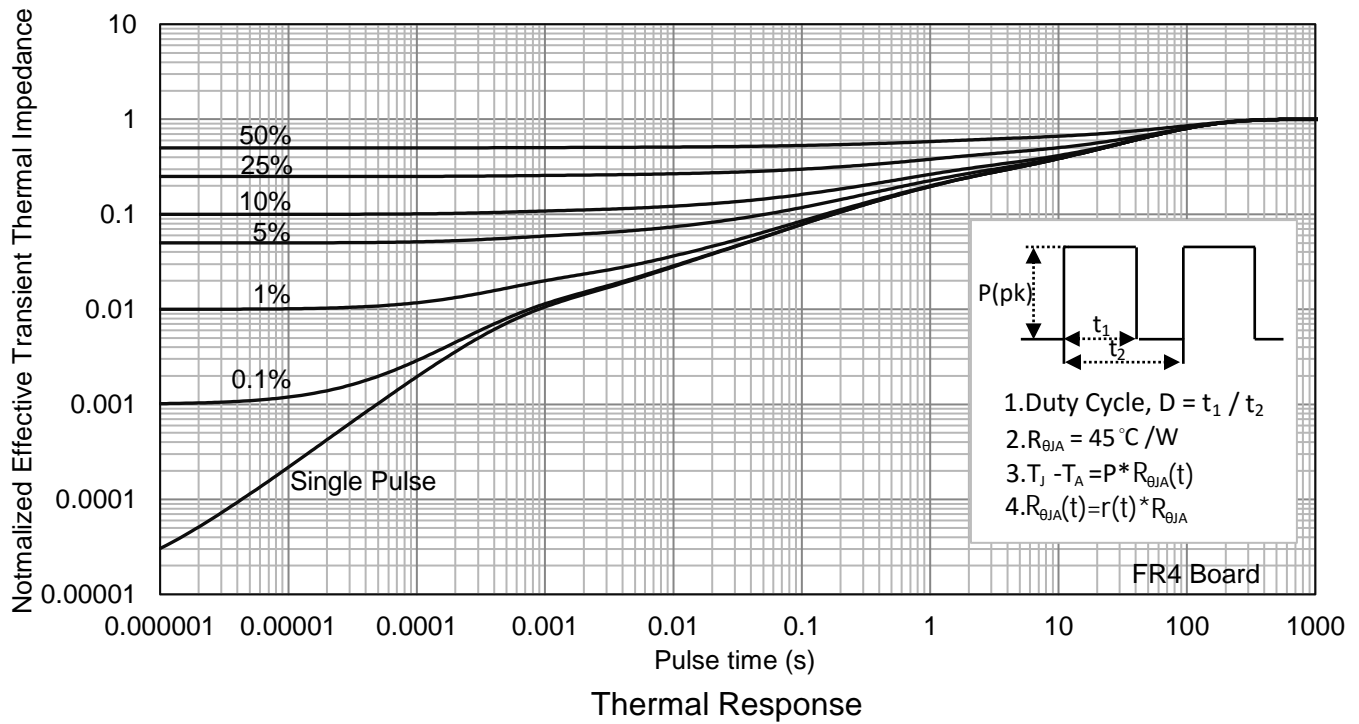
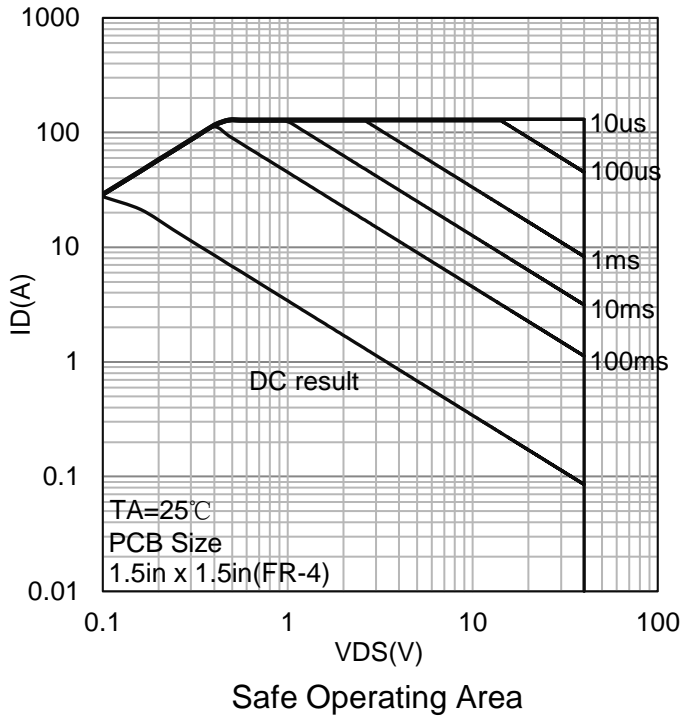
7. ELECTRICAL CHARACTERISTICS CURVES



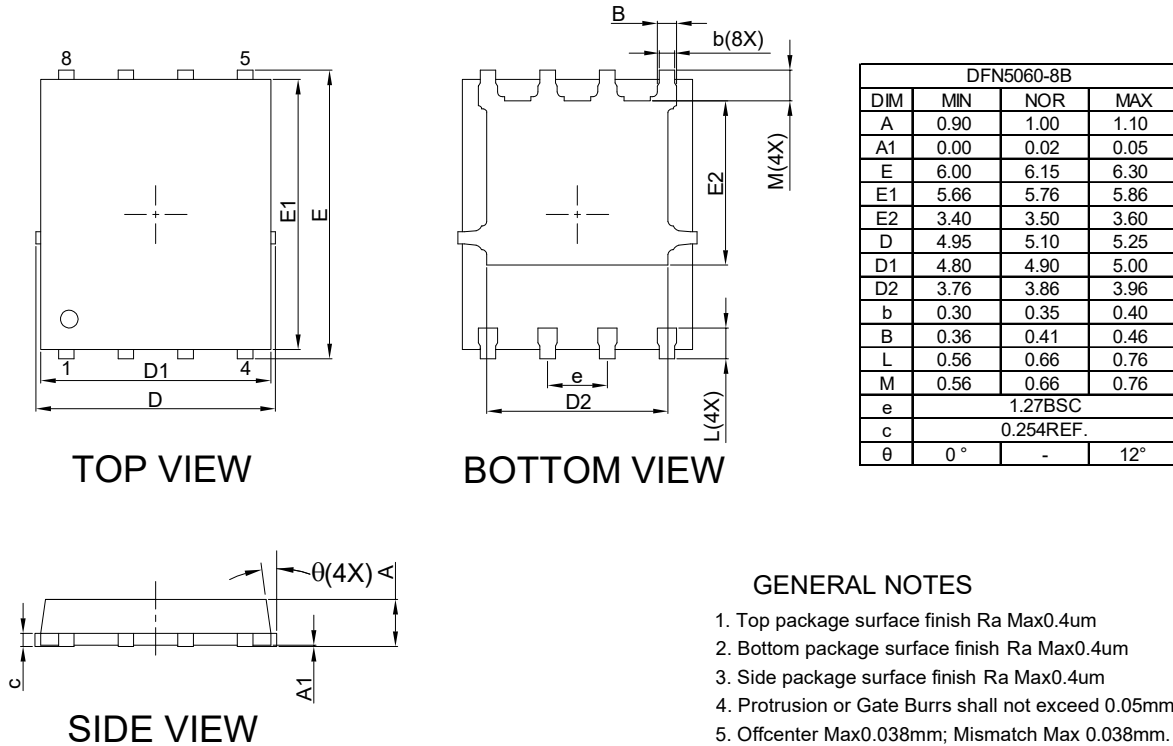
7. ELECTRICAL CHARACTERISTICS CURVES(Con.)



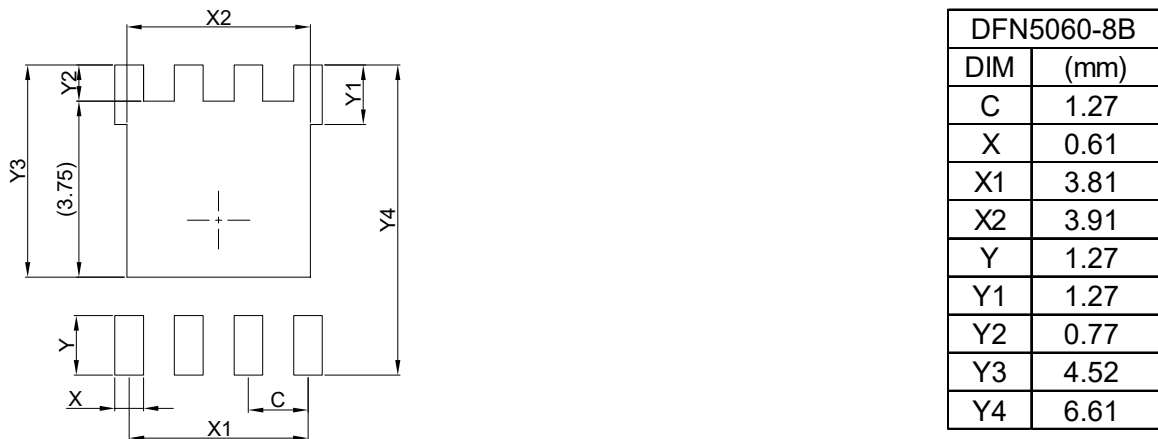
7. ELECTRICAL CHARACTERISTICS CURVES(Con.)



8. OUTLINE AND DIMENSIONS



9. SOLDERING FOOTPRINT



DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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